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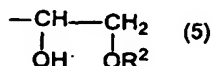
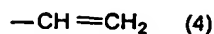
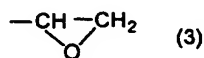
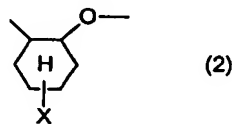
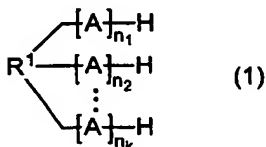
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(54) Title: RADIATION-SENSITIVE NEGATIVE-TYPE RESIST COMPOSITION FOR PATTERN FORMATION AND PATTERN FORMATION METHOD



(57) **Abstract:** The radiation-sensitive negative-type resist composition for pattern formation containing an epoxy resin, a radiation-sensitive cationic polymerization initiator, and a solvent for dissolving the epoxy resin therein, characterized in that the resist composition, through drying, forms a resist film having a softening point falling within a range of 30 to 120 C and that the epoxy resin is represented by formula (1): (wherein R¹ represents a moiety derived from an organic compound having k active hydrogen atoms (k represents an integer of 1 to 100); each of n₁, n₂, through n_k represents 0 or an integer of 1 to 100; the sum of n₁, n₂, through n_k falls within a range of 1 to 100; and each of "A"s, which may be identical to or different from each other, represents an oxycyclohexane skeleton represented by formula (2): (wherein X represents any of groups represented by formulas (3) to (5): and at least two groups represented by formula (3) are contained in one molecule of the epoxy resin)).